

Features

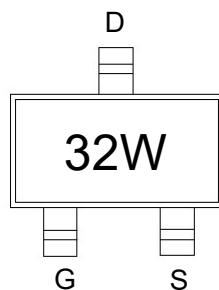
- Trench FET Power MOSFET
- Low Gate Charge

Product Summary

V_{DS}	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30V	480mΩ@10V	0.64A
	700mΩ@4.5V	

Application

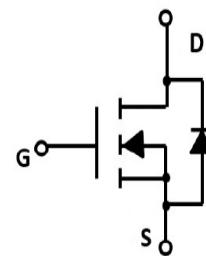
- PWM application
- Load switch



32W: Device code



SOT-323 top view



Schematic diagram

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	Tc=25°C 0.64	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	Tc=25°C 1.5	A
I_D	Continuous Drain Current	Tc=25°C 0.64	A
P_D	Maximum Power Dissipation	Tc=25°C 0.31	W
$R_{θJA}$	Thermal Resistance Junction-Ambient	355	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS1302W	SOT-323	32W	3,000	45,000	180,000	7" reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	--	3	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =0.6A	--	410	480	mΩ
		V _{GS} =4.5V, I _D =0.2A	--	600	700	mΩ

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

C _{ISS}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	46	--	pF
C _{OSS}	Output Capacitance		--	14	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	7	--	pF

Switching Characteristics

Q _g	Total Gate Charge	V _{DS} =15V, I _D =0.6A, V _{GS} =10V	--	0.86	--	nC
Q _{gs}	Gate Source Charge		--	0.24	--	nC
Q _{gd}	Gate Drain Charge		--	0.08	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =15V, I _D =0.5A, V _{GS} =10V, R _G =6Ω	--	5	--	nS
t _r	Turn-on Rise Time		--	8	--	nS
t _{d(off)}	Turn-Off Delay Time		--	8	--	nS
t _f	Turn-Off Fall Time		--	7	--	nS

Source-Drain Diode Characteristics

V _{SD}	Forward on voltage	T _j =25°C, I _S =0.64A	--	--	1.2	V
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Typical Operating Characteristics

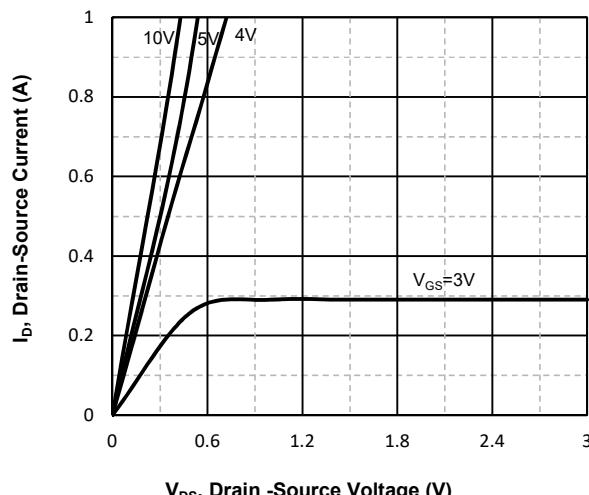


Fig1. Typical Output Characteristics

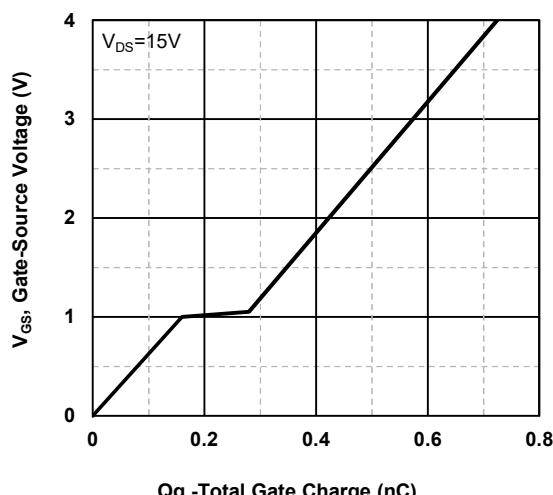


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

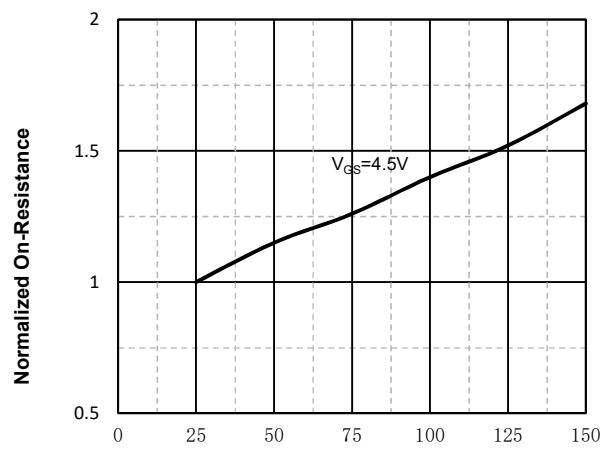


Fig3. Normalized On-Resistance Vs. Temperature

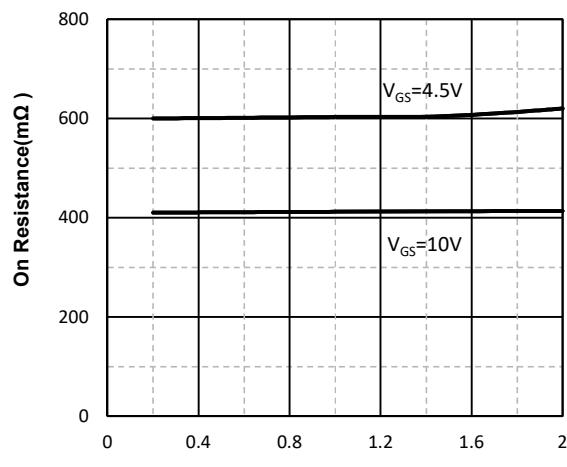


Fig4. On-Resistance Vs. Drain-Source Current

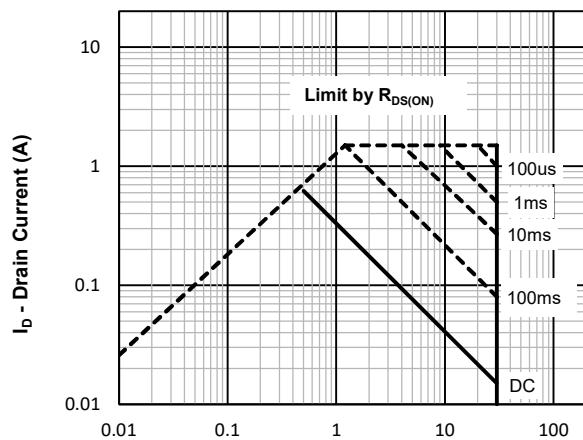


Fig5. Maximum Safe Operating Area

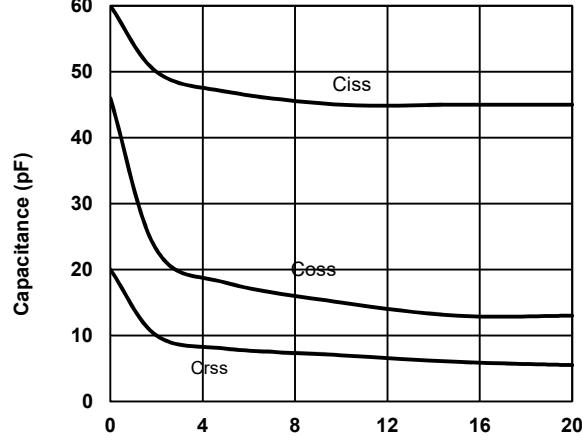
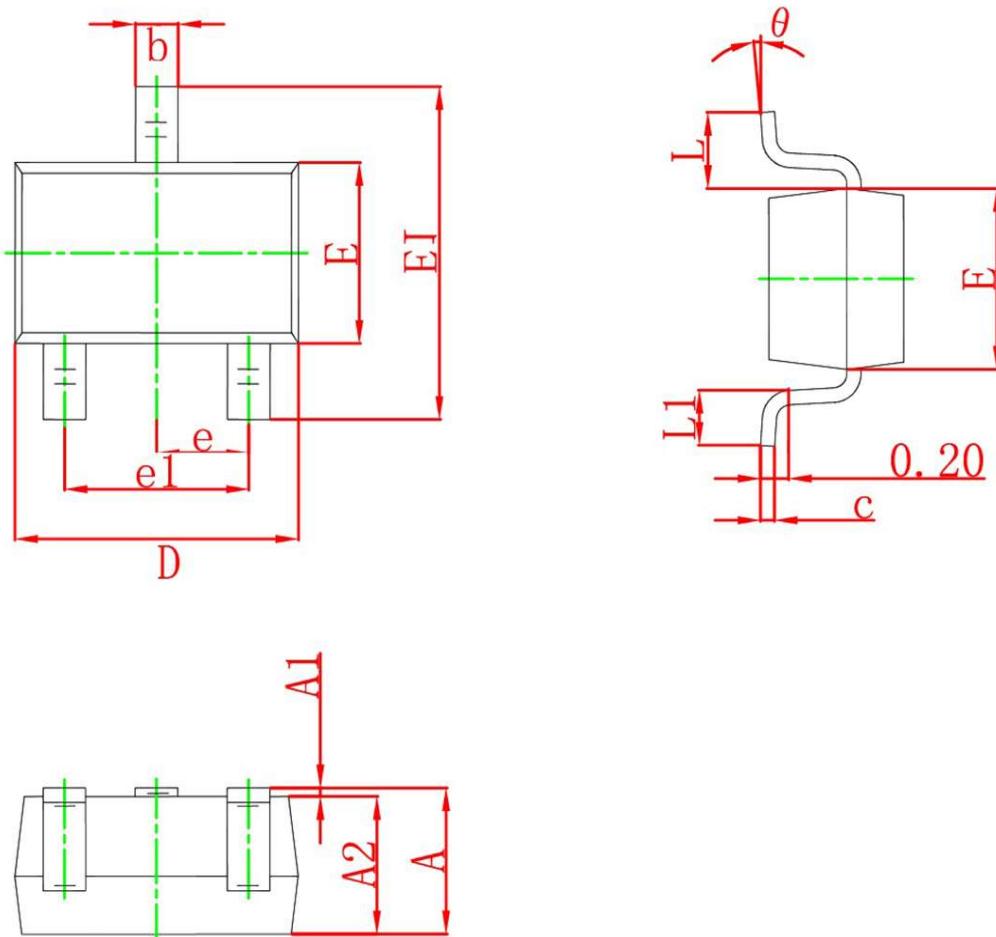


Fig6. Typical Capacitance Vs. Drain-Source Voltage

SOT-323 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°